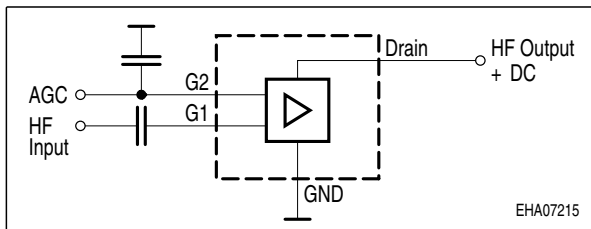
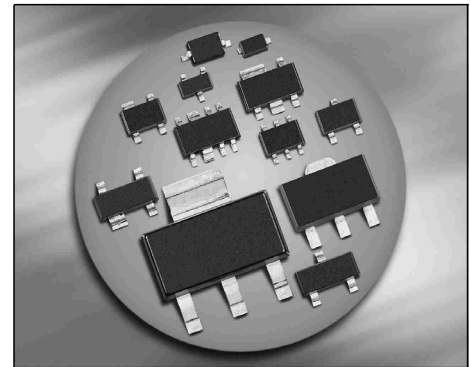


Silicon N-Channel MOSFET Tetrode

- For low noise, high gain controlled input stages up to 1 GHz
- Operating voltage 5V
- Integrated biasing network



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Package	Pin Configuration						Marking
		1=S	2=D	3=G2	4=G1	-	-	
BF1005	SOT143	1=S	2=D	3=G2	4=G1	-	-	MZs
BF1005R	SOT143R	1=D	2=S	3=G1	4=G2	-	-	MZs
BF1005W*	SOT343	1=D	2=S	3=G1	4=G2	-	-	MZ

* on request only

Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	8	V
Continuous drain current	I_D	25	mA
Gate 1/ gate 2-source current	$\pm I_{G1/2SM}$	10	
Gate 1 (external biasing)	$+V_{G1SE}$	3	V
Total power dissipation	P_{tot}		mW
$T_S \leq 76 \text{ }^\circ\text{C}$, BF1005, BF1005R		200	
$T_S \leq 94 \text{ }^\circ\text{C}$, BF1005W		200	
Storage temperature	T_{stg}	-55 ... 150	$^\circ\text{C}$
Channel temperature	T_{ch}	150	

Note:

It is not recommended to apply external DC-voltage on Gate 1 in active mode.

Thermal Resistance

Parameter	Symbol	Value	Unit
Channel - soldering point ¹⁾ BF1005, BF1005R BF1005W	R_{thchs}	≤ 370 ≤ 280	K/W

Electrical Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Drain-source breakdown voltage $I_D = 650 \mu A, V_{G1S} = 0, V_{G2S} = 0$	$V_{(BR)DS}$	12	-	-	V
Gate1-source breakdown voltage $+I_{G1S} = 10 \text{ mA}, V_{G2S} = 0, V_{DS} = 0$	$+V_{(BR)G1SS}$	8	-	12	
Gate2 source breakdown voltage $\pm I_{G2S} = 10 \text{ mA}, V_{G1S} = 0, V_{DS} = 0$	$\pm V_{(BR)G2SS}$	8	-	13	
Gate1-source leakage current $V_{G1S} = 0, V_{G2S} = 6 \text{ V}$	$+I_{G1SS}$	-	100	-	μA
Gate 2 source leakage current $\pm V_{G2S} = 8 \text{ V}, V_{G1S} = 0, V_{DS} = 0$	$\pm I_{G2SS}$	-	-	50	nA
Drain current $V_{DS} = 5 \text{ V}, V_{G1S} = 0, V_{G2S} = 4 \text{ V}$	I_{DSS}	-	-	1.5	mA
Operating current (selfbiased) $V_{DS} = 5 \text{ V}, V_{G2S} = 4 \text{ V}$	I_{DSO}	8	10	16	
Gate2-source pinch-off voltage $V_{DS} = 5 \text{ V}, I_D = 100 \mu A$	$V_{G2S(p)}$	-	1	-	V

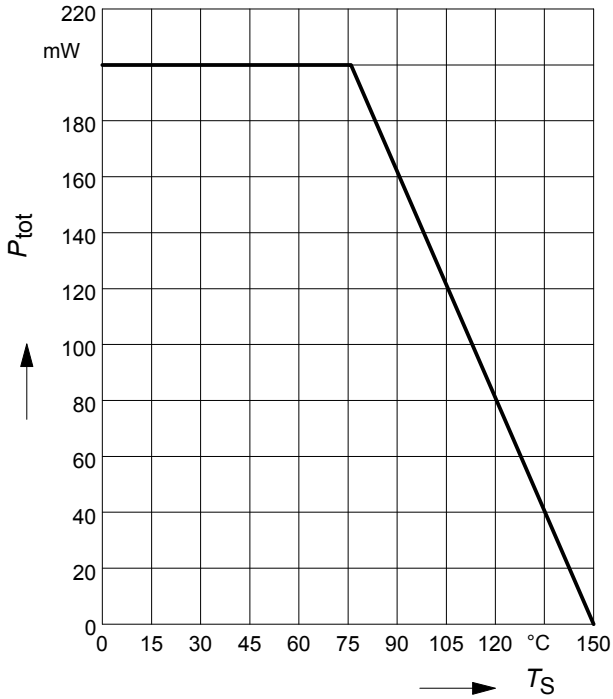
¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Forward transconductance $V_{DS} = 5\text{ V}, V_{G2S} = 4.5\text{ V}$	g_{fs}	20	24	-	mS
Gate1 input capacitance $V_{DS} = 5\text{ V}, V_{G2S} = 4\text{ V}, f = 1\text{ MHz}$	C_{g1ss}	-	2.1	2.5	pF
Output capacitance $V_{DS} = 5\text{ V}, V_{G2S} = 4\text{ V}, f = 100\text{ MHz}$	C_{dss}	-	1.3	-	
Power gain (self biased) $V_{DS} = 5\text{ V}, V_{G2S} = 4\text{ V}, f = 800\text{ MHz}$	G_p	17	19	-	dB
Noise figure $V_{DS} = 5\text{ V}, V_{G2S} = 4\text{ V}, f = 800\text{ MHz}$	F	-	1.6	2.5	dB
Gain control range $V_{DS} = 5\text{ V}, V_{G2S} = 4\text{ V} \dots 0\text{ V}, f = 800\text{ GHz}$	ΔG_p	40	50	-	

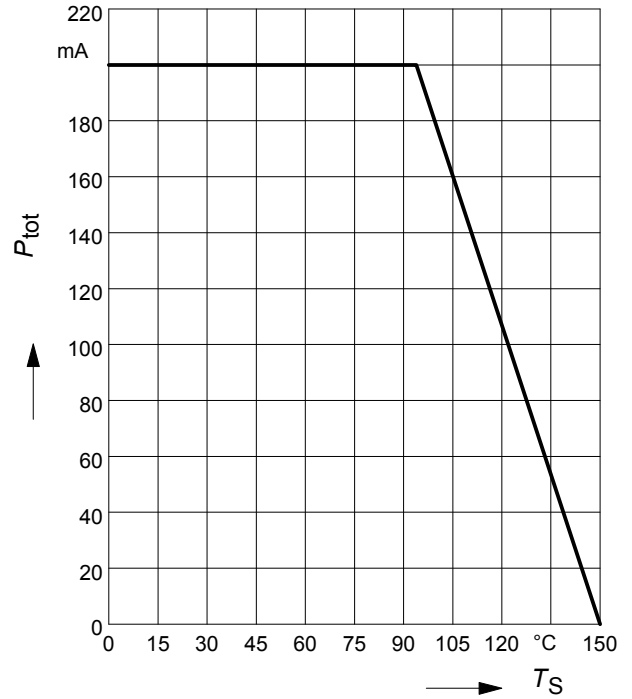
Total power dissipation $P_{tot} = f(T_S)$

BF1005, BF1005R

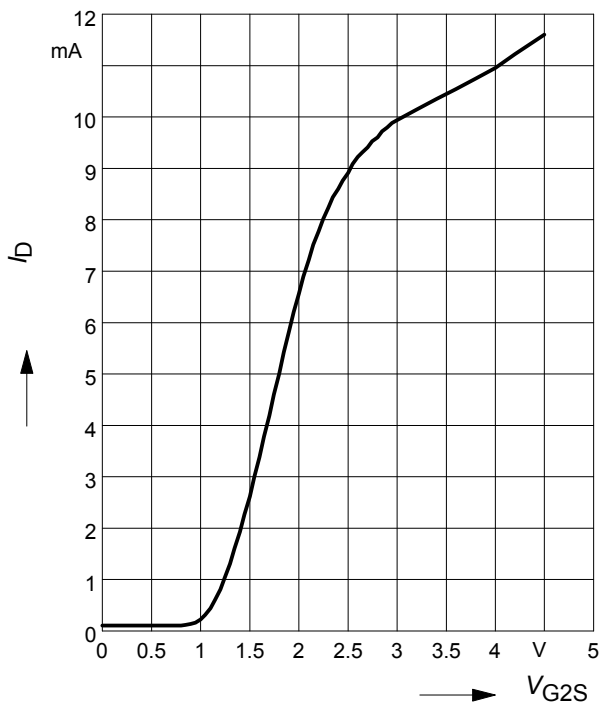


Total power dissipation $P_{tot} = f(T_S)$

BF1005W

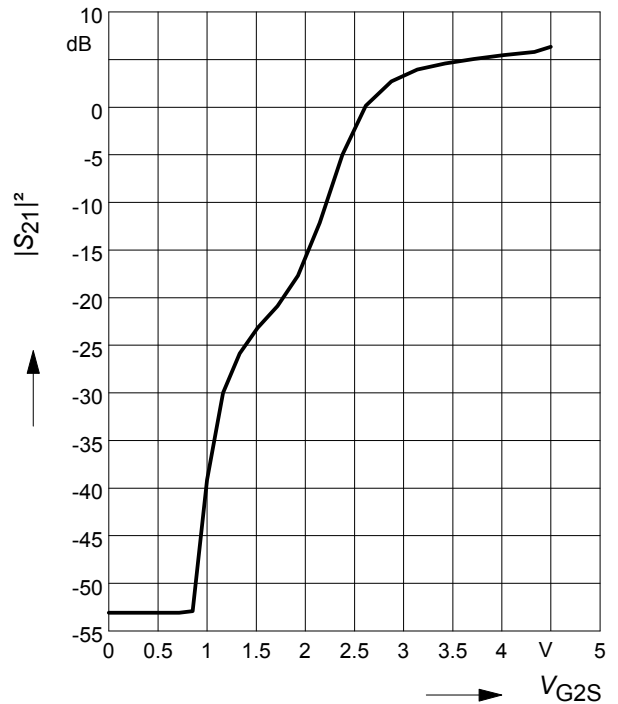


Drain current $I_D = f(V_{G2S})$



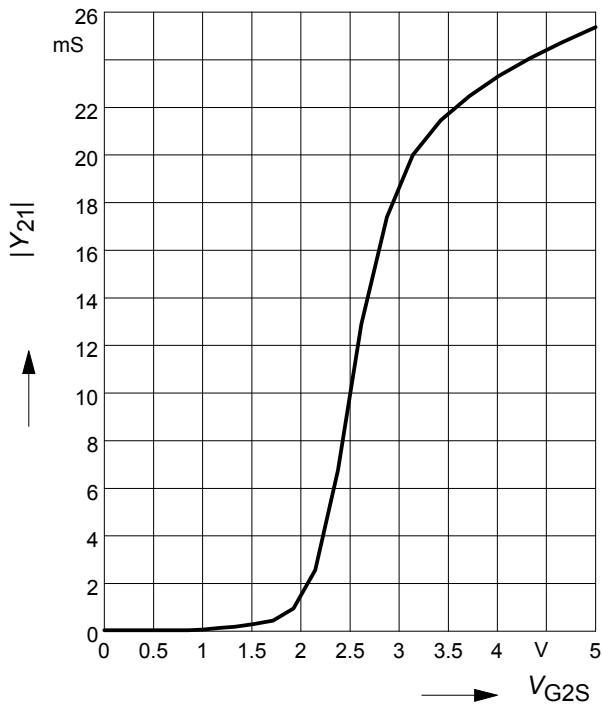
Insertion power gain

$|S_{21}|^2 = f(V_{G2S})$



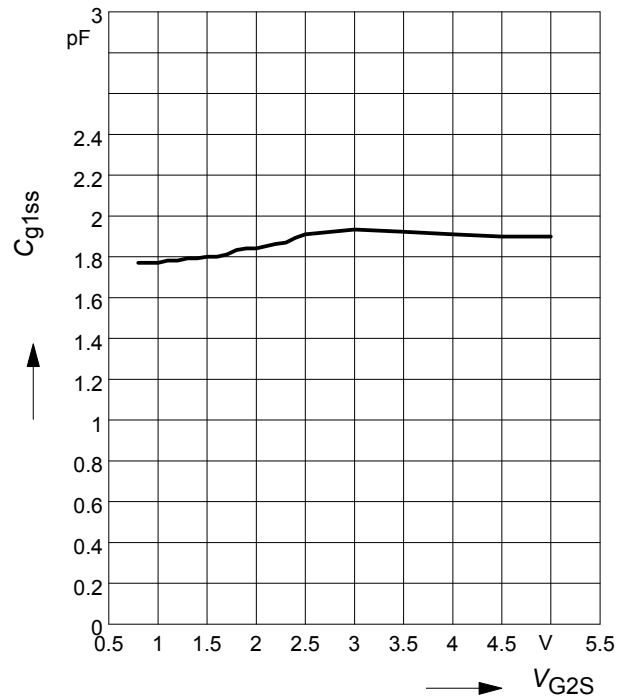
Forward transfer admittance

$|Y_{21}| = f(V_{G2S})$



Gate 1 input capacitance $C_{g1ss} = f(V_{G2S})$

$f = 200\text{MHz}$



Output capacitance $C_{dss} = f(V_{G2S})$

$f = 200\text{MHz}$

